

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (currently amended): A method for forming a dual damascene structure, comprising:

providing a silicon substrate containing one or more electronic devices;

forming a first dielectric layer of a first thickness over said silicon substrate;

forming a first etch stop layer over said first dielectric layer;

forming a second dielectric layer of a second thickness over said first dielectric layer;

forming an anti-reflective coating layer over said second dielectric layer prior to etching of a first trench;

etching a said first trench in said second dielectric layer; and

simultaneously etching a second trench to a first depth in said second dielectric layer and etching said first trench in said first dielectric layer wherein the first depth is approximately equal to the second thickness.

Claim 2 (original): The method of claim 1 wherein said anti-reflective coating layer comprises silicon oxynitride.

Claim 3 (currently amended): The method of claim 1 wherein first ~~and second~~ etch stop ~~layers are~~ layer is formed with material selected from the group consisting of silicon carbide and silicon nitride.

Claim 4 (original): The method of claim 1 wherein said first dielectric layer is FSG.

Claim 5 (original): The method of claim 1 wherein said second dielectric layer is FSG.

Claim 6 (original): The method of claim 1 further comprising:

forming a liner film in said first trench and said second trench; and

forming a contiguous copper layer in said first trench and said second trench.

Claim 7 (currently amended): A method for forming a copper filled dual damascene structure, comprising:

providing a silicon substrate containing one or more electronic devices;

forming a first dielectric layer of a first thickness over said silicon substrate;

forming a first etch stop layer over said first dielectric layer;

forming a second dielectric layer of a second thickness over said first dielectric layer;

forming a silicon oxynitride anti-reflective coating layer over said second dielectric layer prior to etching a first trench in said second dielectric layer;

etching a said first trench to a first depth in said second dielectric layer and said first dielectric layer wherein the first depth is greater than the thickness of said second dielectric layer; and

simultaneously etching a second trench to a second depth in said second dielectric layer and etching said first trench in said first dielectric layer wherein the second depth is approximately equal to the second thickness.

Claim 8 (previously presented): The method of claim 7 wherein said silicon nitride anti-reflective coating layer comprises 30 to 50 atomic percent of silicon, 20 to 50 atomic percent of oxygen, 2 to 17 atomic percent of nitrogen, and 7 to 35 atomic percent of hydrogen.

Claim 9 (currently amended): The method of claim 7 wherein ~~first and second etch stop layers are~~ layer is formed with material selected from the group consisting of silicon carbide and silicon nitride.

Claim 10 (previously presented): The method of claim 7 wherein said first dielectric layer is FSG.

Claim 11 (previously presented): The method of claim 7 wherein said second dielectric layer is FSG.

Claim 12 (previously presented): The method of claim 7 further comprising:

forming a liner film in said first trench and said second trench; and

forming a contiguous copper layer in said first trench and said second trench.